UNISONIC TECHNOLOGIES CO., LTD

BD238

PNP EPITAXIAL SILICON TRANSISTOR

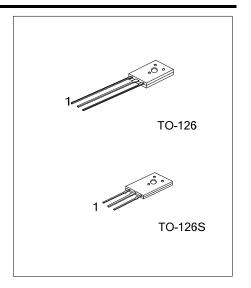
-80V, PNP TRANSISTOR

■ DESCRIPTION

The UTC **BD238** is a PNP epitaxial planar transistor, it uses UTC's advanced technology to provide the customers with high DC current gain and high collector-emitter breakdown voltage, etc.

■ FEATURES

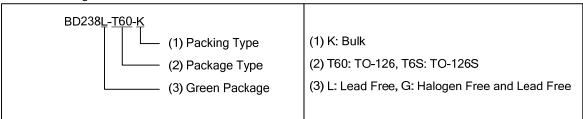
- * High DC current gain
- * High collector-emitter breakdown voltage



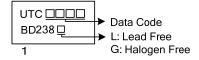
ORDERING INFORMATION

Ordering Number		Dookogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
BD238L-T60-K	BD238G-T60-K	TO-126	Е	С	В	Bulk	
BD238L-T6S-K BD238G-T6S-K		TO-126S	Е	С	В	Bulk	

Note: Pin assignment: E: Emitter B: Base C: Collector



MARKING



<u>www.unisonic.com.tw</u> 1 of 3



UNISONIC TECHNOLOGIES CO., LTD

BD238

PNP EPITAXIAL SILICON TRANSISTOR

ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

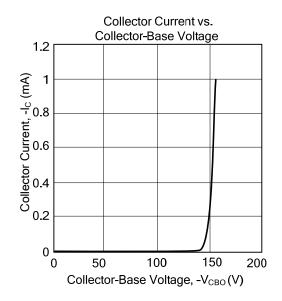
PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V_{CEO}	-80	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	Ic	-2	Α
Collector Power Dissipation	Pc	1.25	W
Junction Temperature	T_J	150	ပ္
Storage Temperature	T _{STG}	-55~150	°C

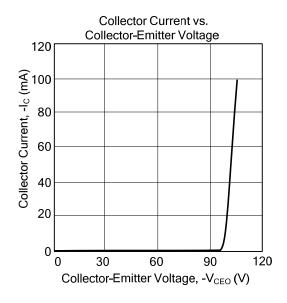
Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

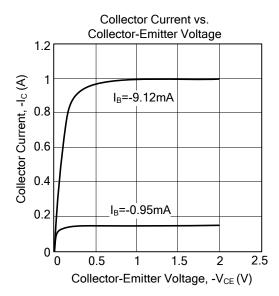
ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	V _{(BR)CBO}	$I_C=-1mA$, $I_E=0$	-100			V
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =-100mA, I _B =0	-80			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_C=-1mA$, $I_E=0$	-5			V
Collector Cut-Off Current	I _{CBO}	V _{CB} =-100V, I _E =0			-100	μΑ
Emitter Cut-Off Current	I _{EBO}	V_{EB} =-5 V , I_{C} =0			-1	mA
DC Commant Cain	h _{FE(1)}	V _{CE} =-2V, I _C =-150mA	40			
DC Current Gain	h _{FE(2)}	V_{CE} =-2V, I_{C} =-1A	25			
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =-1A, I _B =-100mA			-0.6	V
Transition Frequency	f _T	V _{CE} =-10V, I _C =-250mA, f=10MHz	3			MHz

■ TYPICAL CHARACTERISTICS







UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by Unisonic manufacturer:

Other Similar products are found below:

BC559C MCH4017-TL-H MMBT-2369-TR BC546/116 NJVMJD148T4G NTE16 NTE195A IMX9T110 2N4401-A 2N4403 2N6728

2SA1419T-TD-H 2SA2126-E 2SB1204S-TL-E FMC5AT148 2N2369ADCSM 2N2907A 2N3904-NS 2N5769 2SC4618TLN CPH6501
TL-E MCH4021-TL-E Jantx2N5416 US6T6TR BAX18/A52R BC556/112 IMZ2AT108 MMST8098T146 UMX21NTR MCH6102-TL-E

TTA1452B,S4X(S 2N3879 NTE13 NTE282 NTE323 NTE350 NTE81 JANTX2N2920L JANTX2N3735 JANSR2N2222AUB

CMLT3946EG TR SNSS40600CF8T1G CMLT3906EG TR GRP-DATA-JANS2N2907AUB GRP-DATA-JANS2N2222AUA

MMDT3946FL3-7 2N4240 MSB30KH-13 2N2221AUB 2SD1815T-TL-E